P-Ch 18V Fast Switching MOSFETs

★ Super Low Gate Charge
★ Green Device Available
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

Green

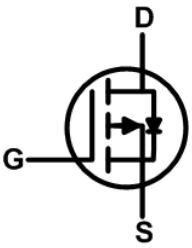
BVDSS	RDSON	ID
-18V	17mΩ	-7A

Description

The XR2313L is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications The XR2313L meet the RoHS and Green Product requirement with full function reliability approved.

SOT23-3L Pin Configurations





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-18	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -4.5V[1]	-7	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -4.5V[1]	-4	A
I_{DM}	Pulsed Drain Current[2]	-28	A
P_D@T_A=25℃	Total Power Dissipation[3]	1.28	W
P_D@T_A=70℃	Total Power Dissipation[3]	---	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	125	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	---	---	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-15	-18	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -15V V_{GS}=0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-0.4	-0.6	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}= -4.5V, I_D= -5.1A	-	17	24	mΩ
		V_{GS}= -2.5V, I_D= -3.75A	-	24	32	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -10V, V_{GS}=0V, f=1.0MHz	-	830	-	pF
C_{oss}	Output Capacitance		-	132	-	pF
C_{rss}	Reverse Transfer Capacitance		-	85	-	pF
Q_g	Total Gate Charge	V_{DS}= -10V, I_D= -2.5A, V_{GS}= -4.5V	-	8.8	-	nC
Q_{gs}	Gate-Source Charge		-	1.4	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	1.9	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -10V, I_D= -4.3A, R_G= 1Ω, V_{GEN}= -4.5V	-	10	-	ns
t_r	Turn-on Rise Time		-	32	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	50	-	ns
t_f	Turn-off Fall Time		-	51	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-7	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-32	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -5.1A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure1: Output Characteristics

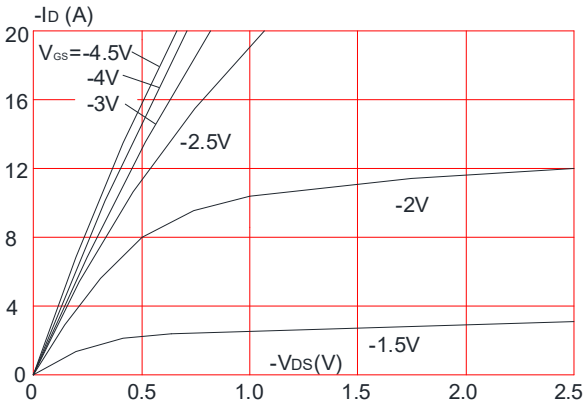


Figure 2: Typical Transfer Characteristics

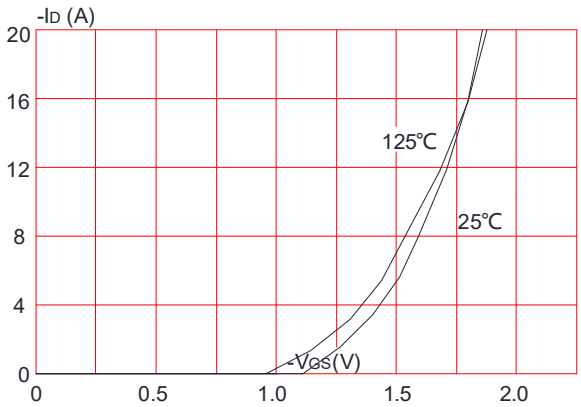


Figure 3: On-resistance vs. Drain Current

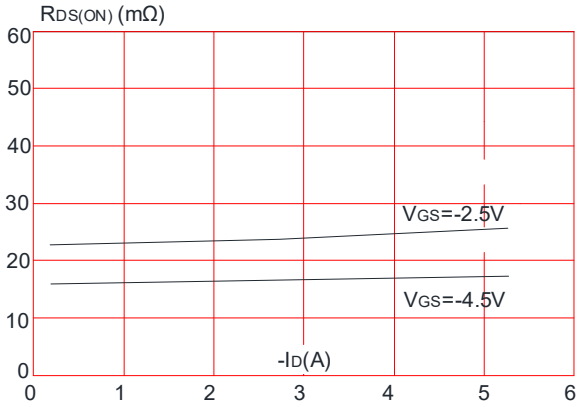


Figure 4: Body Diode Characteristics

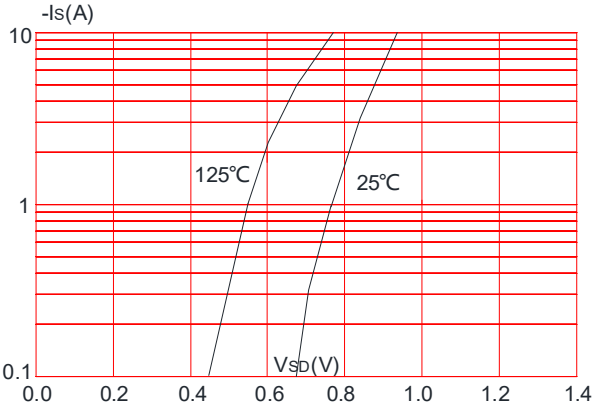


Figure 5: Gate Charge Characteristics

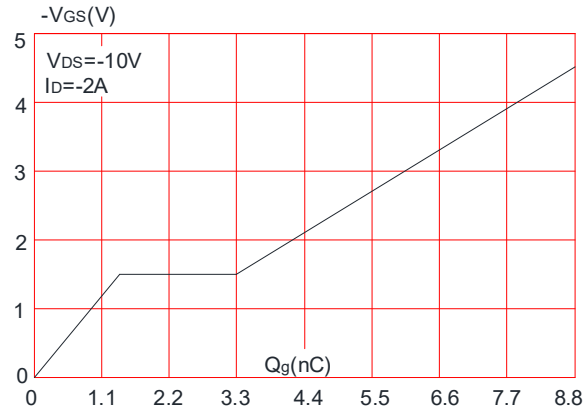


Figure 6: Capacitance Characteristics

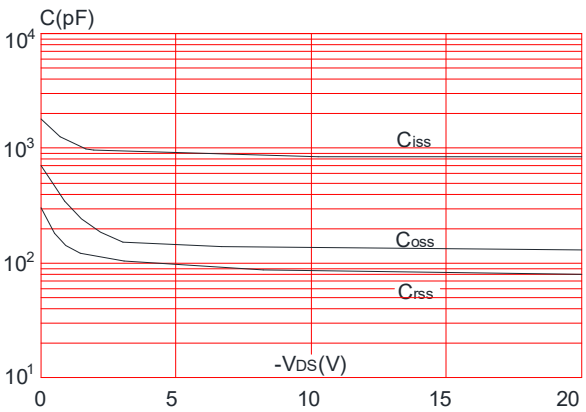


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

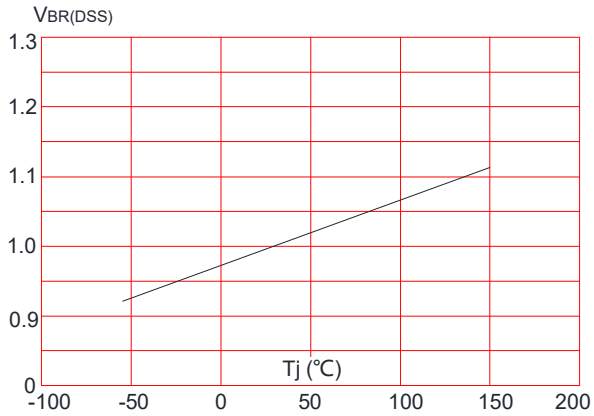


Figure 8: Normalized on Resistance vs. Junction Temperature

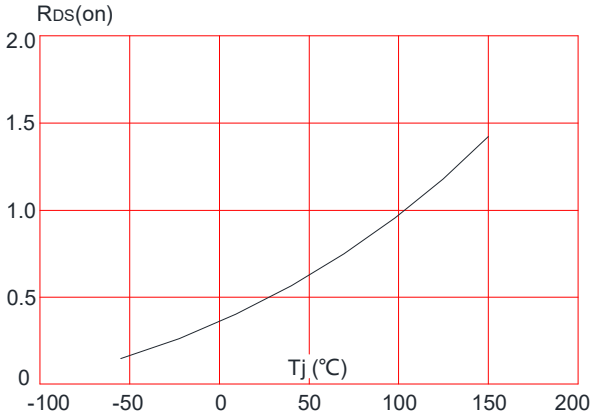


Figure 9: Maximum Safe Operating Area

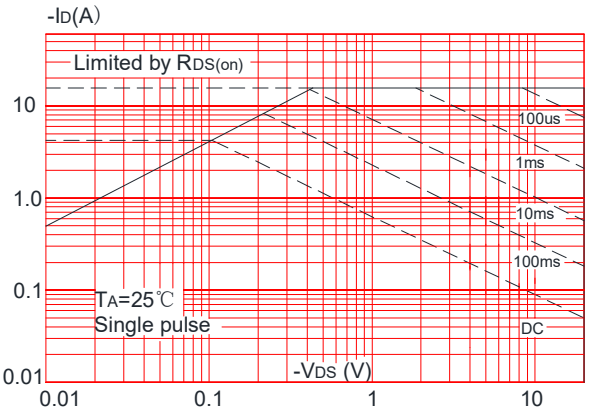


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

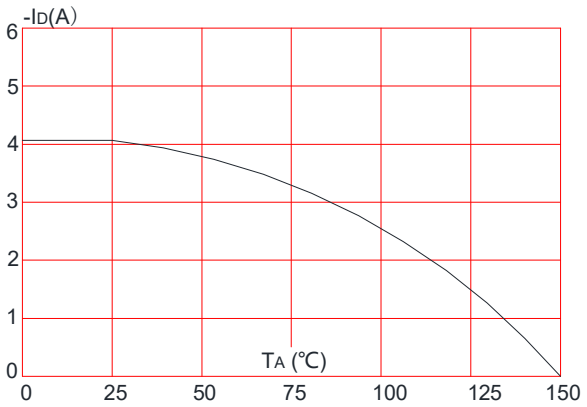
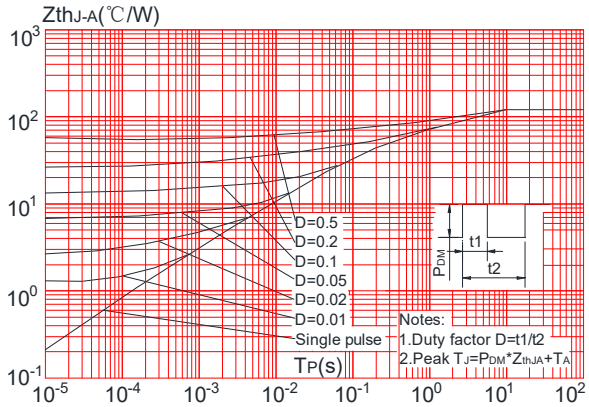
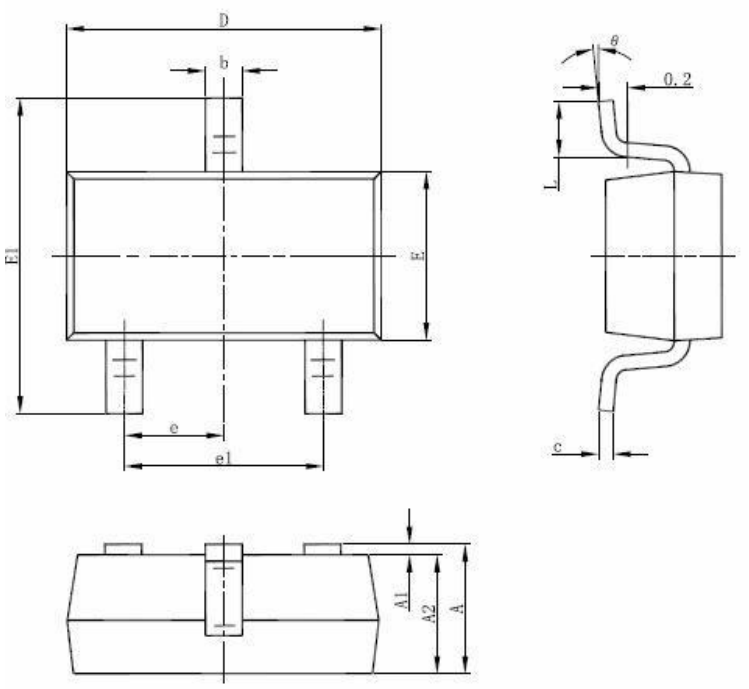


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°